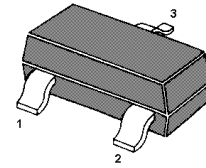


MMBT8550 (1.5A)-AH

PNP Silicon Epitaxial Planar Transistor

for switching and amplifier applications. Especially suitable for AF-driver stages and low power output stages.

As complementary type the NPN transistor MMBT8050 (1.5A) is recommended.



1.BASE 2.EMITTER 3.COLLECTOR
TO-236 Plastic Package

Features

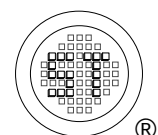
- AEC-Q101 Qualified and PPAP Capable
- Halogen and Antimony Free(HAF), RoHS compliant

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	40	V
Collector Emitter Voltage	$-V_{CEO}$	25	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	1.5	A
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 1\text{ V}$, $-I_C = 100\text{ mA}$	h_{FE}	100	250	-
MMBT8550C	h_{FE}	160	400	-
MMBT8550D	h_{FE}	40	-	-
at $-V_{CE} = 1\text{ V}$, $-I_C = 800\text{ mA}$				
Collector Base Cutoff Current at $-V_{CB} = 35\text{ V}$	$-I_{CBO}$	-	100	nA
Emitter Base Cutoff Current at $-V_{EB} = 6\text{ V}$	$-I_{EBO}$	-	100	nA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	40	-	V
Collector Emitter Breakdown Voltage at $-I_C = 2\text{ mA}$	$-V_{(BR)CEO}$	25	-	V
Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage at $-I_C = 800\text{ mA}$, $-I_B = 80\text{ mA}$	$-V_{CE(sat)}$	-	0.5	V
Base Emitter Saturation Voltage at $-I_C = 800\text{ mA}$, $-I_B = 80\text{ mA}$	$-V_{BE(sat)}$	-	1.2	V
Base Emitter Voltage at $-V_{CE} = 1\text{ V}$, $-I_C = 10\text{ mA}$	$-V_{BE(on)}$	-	1	V
Gain Bandwidth Product at $-V_{CE} = 10\text{ V}$, $-I_C = 50\text{ mA}$	f_T	120	-	MHz



MMBT8550 (1.5A)-AH

